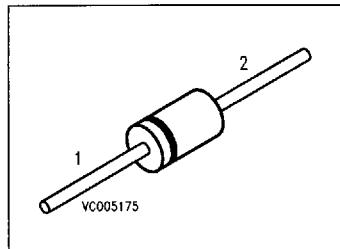


## Silicon RF Switching Diodes

BA 282  
BA 283

- For low-loss VHF band switching in TV tuners
- Not for new design



Type	Marking	Ordering Code	Pin Configuration	Package <sup>1)</sup>
BA 282	yellow	Q62702-A428		DO-35 DHD
BA 283		Q62702-A429		

### Maximum Ratings

Parameter	Symbol	Values	Unit
Reverse voltage	$V_R$	35	V
Forward current, $T_A \leq 60^\circ\text{C}$	$I_F$	100	mA
Junction temperature	$T_J$	150	$^\circ\text{C}$
Storage temperature range	$T_{stg}$	- 55 ... + 150	

### Thermal Resistance

Junction - ambient	$R_{th\ JA}$	$\leq 400$	K/W
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1) For detailed information see chapter Package Outlines.

**Electrical Characteristics**at  $T_A = 25^\circ\text{C}$ , unless otherwise specified.

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
Forward voltage $I_F = 100 \text{ mA}$	$V_F$	—	—	1	V
Reverse current $V_R = 20 \text{ V}$	$I_R$	—	—	50	nA
Diode capacitance $f = 1 \text{ MHz}$ BA 282: $V_R = 1 \text{ V}$ $V_R = 3 \text{ V}$ BA 283: $V_R = 1 \text{ V}$ $V_R = 3 \text{ V}$	$C_T$	—	—	1.5 1.2 1.5 1	pF
Forward resistance $f = 100 \text{ MHz}$ BA 282: $I_F = 3 \text{ mA}$ $I_F = 10 \text{ mA}$ BA 283: $I_F = 3 \text{ mA}$ $I_F = 10 \text{ mA}$	$r_f$	—	—	0.7 0.5 1.2 0.9	$\Omega$
Reverse resistance $V_R = 1 \text{ V}, f = 100 \text{ MHz}$	$1/g_P$	—	100	—	k $\Omega$
Series inductance	$L_s$	—	2.5	—	nH